

COMPLEMENTARY PAIR SMALL SIGNAL SURFACE MOUNT TRANSISTOR

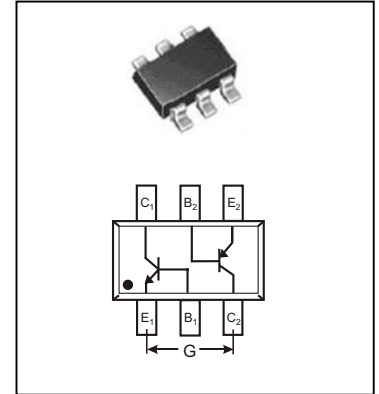
Features

- Epitaxial Die Construction
- Two internal isolated NPN/PNP Transistors in one package
- Ultra-Small Surface Mount Package

Mechanical Data

- Case: SOT-363, Molded Plastic
- Case material - UL Flammability Rating Classification 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking (See Page 3): K7P
- Ordering & Date Code Information: See Page 3
- Weight: 0.006 grams (approx.)

BC847PN



SOT-363

Maximum Ratings @ T_A = 25°C unless otherwise specified **Total Device**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P _d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150	°C

Maximum Ratings @ T_A = 25°C unless otherwise specified **NPN BC847B Section**

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	100	mA
Peak Collector Current	I _{CM}	200	mA
Peak Emitter Current	I _{EM}	200	mA

Maximum Ratings @ T_A = 25°C unless otherwise specified **PNP BC857B Section**

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current	I _C	-100	mA
Peak Collector Current	I _{CM}	-200	mA
Peak Emitter Current	I _{EM}	-200	mA

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified **NPN BC847B Section**

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage (Note 2)	$V_{(BR)CBO}$	50	—	—	V	$I_C = 10\mu\text{A}, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 2)	$V_{(BR)CEO}$	45	—	—	V	$I_C = 10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage (Note 2)	$V_{(BR)EBO}$	6	—	—	V	$I_E = 1\mu\text{A}, I_C = 0$
DC Current Gain (Note 2)	h_{FE}	200	290	450	—	$V_{CE} = 5.0\text{V}, I_C = 2.0\text{mA}$
Collector-Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	—	90 200	250 600	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	—	700 900	—	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Voltage (Note 2)	$V_{BE(ON)}$	580 —	660 —	700 720	mV	$V_{CE} = 5.0\text{V}, I_C = 2.0\text{mA}$ $V_{CE} = 5.0\text{V}, I_C = 10\text{mA}$
Collector-Cutoff Current (Note 2)	I_{CBO} I_{CBO}	— —	— —	15 5.0	nA μA	$V_{CB} = 30\text{V}$ $V_{CB} = 30\text{V}, T_A = 150^\circ\text{C}$
Gain Bandwidth Product	f_T	100	300	—	MHz	$V_{CE} = 5.0\text{V}, I_C = 10\text{mA}$, $f = 100\text{MHz}$
Collector-Base Capacitance	C_{CBO}	—	3.5	6.0	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}$
Noise Figure	NF	—	2.0	10	dB	$V_{CE} = 5\text{V}, I_C = 200\mu\text{A}$, $R_G = 2.0\text{k}\Omega$, $f = 1.0\text{kHz}, \Delta f = 200\text{Hz}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified **PNP BC857B Section**

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage (Note 2)	$V_{(BR)CBO}$	-50	—	—	V	$I_C = 10\mu\text{A}, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 2)	$V_{(BR)CEO}$	-45	—	—	V	$I_C = 10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage (Note 2)	$V_{(BR)EBO}$	-5	—	—	V	$I_E = 1\mu\text{A}, I_C = 0$
DC Current Gain (Note 2)	h_{FE}	220	290	475	—	$V_{CE} = 5.0\text{V}, I_C = 2.0\text{mA}$
Collector-Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	—	-75 -250	-300 -650	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	—	-700 -850	— -950	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Voltage (Note 2)	$V_{BE(ON)}$	-600 —	-650 —	-750 -820	mV	$V_{CE} = 5.0\text{V}, I_C = 2.0\text{mA}$ $V_{CE} = 5.0\text{V}, I_C = 10\text{mA}$
Collector-Cutoff Current (Note 2)	I_{CBO} I_{CBO}	— —	— —	-15 -4.0	nA μA	$V_{CB} = 30\text{V}$ $V_{CB} = 30\text{V}, T_A = 150^\circ\text{C}$
Gain Bandwidth Product	f_T	100	200	—	MHz	$V_{CE} = 5.0\text{V}, I_C = 10\text{mA}$, $f = 100\text{MHz}$
Collector-Base Capacitance	C_{CBO}	—	3	4.5	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}$
Noise Figure	NF	—	—	10	dB	$V_{CE} = 5\text{V}, I_C = 200\mu\text{A}$, $R_G = 2.0\text{k}\Omega$, $f = 1.0\text{kHz}, \Delta f = 200\text{Hz}$

Notes: 2. Short duration pulse test used to minimize self-heating effect.